

**VHF power transistor**

**BLV11**

**Description:**

N-P-N silicon planar epitaxial transistor intended for use in class-A, B and C operated mobile, HF and VHF transmitters with a nominal supply voltage of 13.5 V. The transistor is resistance stabilized and is guaranteed to withstand severe load mismatch conditions with a supply over-voltage to 16.5 V.

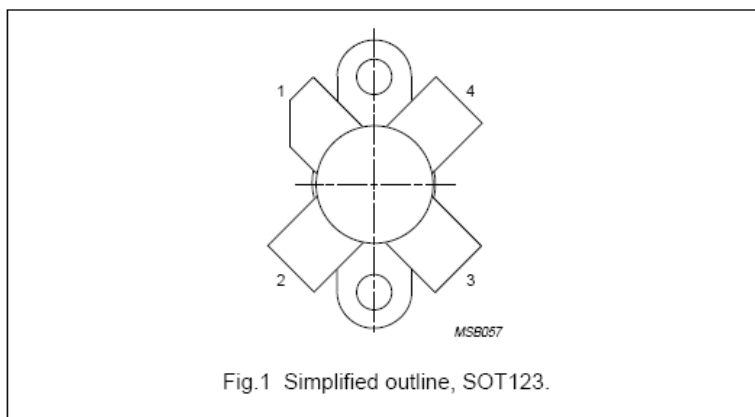
**Features:**

It has a 3/8" flange envelope with a ceramic cap. All leads are isolated from the flange.

**Specifications:**

| MODE OF OPERATION | V <sub>CE</sub><br>V | f<br>MHz | P <sub>L</sub><br>W | G <sub>p</sub><br>dB | η<br>%  | $\bar{z}_i$<br>Ω | $\bar{Y}_L$<br>mS |
|-------------------|----------------------|----------|---------------------|----------------------|---------|------------------|-------------------|
| c.w.              | 13,5                 | 175      | 15                  | > 8,0                | > 60    | 2,3 + j2,2       | 130 - j4,4        |
| c.w.              | 12,5                 | 175      | 15                  | typ. 7,5             | typ. 67 | -                | -                 |

**Drawings:**



| PIN | DESCRIPTION |
|-----|-------------|
| 1   | collector   |
| 2   | emitter     |
| 3   | base        |
| 4   | emitter     |